



AMPLIFIER TRANSISTOR

Collector-Emitter Voltage: $V_{ce}=150V$.

Collector Dissipation: $P_c(max)=625mW$

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$)

T_{stg} — Storage Temperature..... $-55\sim 150^{\circ}C$

T_j — Junction Temperature..... $150^{\circ}C$

P_C — Collector Dissipation..... $625mW$

V_{CBO} — Collector-Base Voltage..... $-160V$

V_{CEO} — Collector-Emitter Voltage..... $-150V$

V_{EBO} — Emitter-Base Voltage..... $-5V$

I_C — Collector Current..... $-600mA$

TO-92



1—Emitter, E

2—Base, B

3—Collector, C

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-160			V	$I_C=-100\mu A$, $I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	-150			V	$I_C=-1mA$, $I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	$I_E=-10\mu A$, $I_C=0$
I_{CBO}	Collector Cut-off Current			-50	nA	$V_{CB}=-120V$, $I_E=0$
I_{EBO}	Emitter-Base Cut-off Current			-50	nA	$V_{EB}=-3V$, $I_C=0$
H_{FE} (1)	DC Current Gain	30				$V_{CE}=-5V$, $I_C=-1mA$
H_{FE} (2)		60		280		$V_{CE}=-5V$, $I_C=-10mA$
H_{FE} (3)		50				$V_{CE}=-5V$, $I_C=-50mA$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			-0.2	V	$I_C=-10mA$, $I_B=-1mA$
$V_{CE(sat2)}$				-0.5	V	$I_C=-50mA$, $I_B=-5mA$
$V_{BE(sat1)}$	Base-Emitter Saturation Voltage			-1	V	$I_C=-10mA$, $I_B=-1mA$
$V_{BE(sat2)}$				-1	V	$I_C=-50mA$, $I_B=-5mA$,
f_T	Current Gain-Bandwidth Product	100		400	MHz	$V_{CE}=-10V$, $I_C=-10mA$ $F=100MHz$